

Application Data Sheet**Applicant Information**

Applicant Authority type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Masahiro
Family Name::	SAKURADA
City of Residence::	Fukushima
Country of Residence::	JAPAN

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Izumi
Family Name::	FUSEGAWA
City of Residence::	Fukushima
Country of Residence::	JAPAN

Correspondence Information

Correspondence Customer Number::	25944
----------------------------------	-------

Application Information

Application Type::	National Phase
Subject Matter::	Utility
CD-ROM or CD-R::	None
Title::	METHOD OF PRODUCING P-DOPED SILICON SINGLE CRYSTAL AND P- DOPED N-TYPE SILICON SINGLE CRYSTAL WAFER
Attorney Docket Number::	124231
Suggested Drawing Figure::	
Total Drawing Sheets::	4
Small Entity::	No

Representative Information

10/538878

JC17 Rec'd PCT/PTO 14 JUN 2005

James A. Oliff, Reg. No. 27,075

William P. Berridge, Reg. No. 30,024

Thomas J. Pardini, Reg. No. 30,411

Edward P. Walker, Reg. No. 31,450

Robert A. Miller, Reg. No. 32,771

Mario A. Costantino, Reg. No. 33,565

Kirk M. Hudson, Reg. No. 27,562

Domestic Priority Information			
Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application is a	National Stage of	PCT/JP03/016794	12/25/03
Foreign Priority Information			
Country::	Application Number::	Filing Date::	Priority Claimed::
JAPAN	2003-10436	1/17/03	Yes
Assignee Information			
Assignee Name::		SHIN-ETSU HANDOTAI CO., LTD.	
Street of mailing address::		4-2, Marunouchi 1-chome,	
City of mailing address::		Chiyoda-ku,	
State or Province of mailing address::		Tokyo,	
Country of mailing address::		JAPAN	